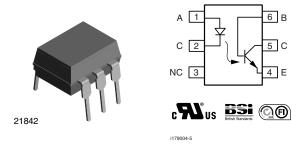
### Vishay Semiconductors



### **Optocoupler, Phototransistor Output, with Base Connection**



#### **DESCRIPTION**

The 4N25 family is an industry standard single channel phototransistor coupler. This family includes the 4N25, 4N26, 4N27, 4N28. Each optocoupler consists of gallium arsenide infrared LED and a silicon NPN phototransistor.

#### **FEATURES**

- Isolation test voltage 5000 V<sub>RMS</sub>
- Interfaces with common logic families
- Input-output coupling capacitance < 0.5 pF
- Industry standard dual-in-line 6 pin package
- Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC





#### **APPLICATIONS**

- AC mains detection
- · Reed relay driving
- Switch mode power supply feedback
- Telephone ring detection
- · Logic ground isolation
- Logic coupling with high frequency noise rejection

#### **AGENCY APPROVALS**

- UL1577, file no. E52744
- BSI: EN 60065:2002, EN 60950:2000
- FIMKO: EN 60950, EN 60065, EN 60335

| ORDER INFORMATION |                   |  |  |  |
|-------------------|-------------------|--|--|--|
| PART              | REMARKS           |  |  |  |
| 4N25              | CTR > 20 %, DIP-6 |  |  |  |
| 4N26              | CTR > 20 %, DIP-6 |  |  |  |
| 4N27              | CTR > 10 %, DIP-6 |  |  |  |
| 4N28              | CTR > 10 %, DIP-6 |  |  |  |

| ABSOLUTE MAXIMUM RATINGS (1)        |                |                   |       |      |  |  |  |
|-------------------------------------|----------------|-------------------|-------|------|--|--|--|
| PARAMETER                           | TEST CONDITION | SYMBOL            | VALUE | UNIT |  |  |  |
| INPUT                               |                |                   |       |      |  |  |  |
| Reverse voltage                     |                | V <sub>R</sub>    | 5     | V    |  |  |  |
| Forward current                     |                | I <sub>F</sub>    | 60    | mA   |  |  |  |
| Surge current                       | t ≤ 10 µs      | I <sub>FSM</sub>  | 3     | Α    |  |  |  |
| Power dissipation                   |                | P <sub>diss</sub> | 100   | mW   |  |  |  |
| ОUТРUТ                              |                |                   |       |      |  |  |  |
| Collector emitter breakdown voltage |                | $V_{CEO}$         | 70    | V    |  |  |  |
| Emitter base breakdown voltage      |                | V <sub>EBO</sub>  | 7     | V    |  |  |  |
| Collector current                   |                | I <sub>C</sub>    | 50    | mA   |  |  |  |
|                                     | t ≤ 1 ms       | I <sub>C</sub>    | 100   | mA   |  |  |  |
| Power dissipation                   |                | P <sub>diss</sub> | 150   | mW   |  |  |  |



## Optocoupler, Phototransistor Output, Vishay Semiconductors with Base Connection

| ABSOLUTE MAXIMUM RATINGS (1)                     |   |                  |                  |           |  |  |  |
|--|---|------------------|------------------|-----------|--|--|--|
| PARAMETER  | TEST CONDITION  | SYMBOL           | VALUE            | UNIT      |  |  |  |
| COUPLER  |   |                  |                  |           |  |  |  |
| Isolation test voltage                           |   | $V_{ISO}$        | 5000             | $V_{RMS}$ |  |  |  |
| Creepage distance                                |   |                  | ≥ 7              | mm        |  |  |  |
| Clearance distance                               |   |                  | ≥ 7              | mm        |  |  |  |
| Isolation thickness between emitter and detector |   |                  | ≥ 0.4            | mm        |  |  |  |
| Comparative tracking index                       | DIN IEC 112/VDE 0303, part 1                                    |                  | 175              |           |  |  |  |
| Isolation resistance                             | V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 25 °C               | R <sub>IO</sub>  | 10 <sup>12</sup> | Ω         |  |  |  |
| isolation resistance                             | V <sub>IO</sub> = 500 V, T <sub>amb</sub> = 100 °C              | R <sub>IO</sub>  | 10 <sup>11</sup> | Ω         |  |  |  |
| Storage temperature                              |   | T <sub>stg</sub> | - 55 to + 125    | °C        |  |  |  |
| Operating temperature                            |   | T <sub>amb</sub> | - 55 to + 100    | °C        |  |  |  |
| Junction temperature                             |   | T <sub>j</sub>   | 125              | °C        |  |  |  |
| Soldering temperature (2)                        | max.10 s dip soldering: distance to seating plane $\geq$ 1.5 mm |                  | 260              | °C        |  |  |  |

#### **Notes**

<sup>(2)</sup> Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering condditions for through hole devices (DIP).

| ELECTRICAL CHARACTERISTICS (1)          |  |      |                      |      |      |      |      |  |
|---|--|------|----------------------|------|------|------|------|--|
| PARAMETER                               | TEST CONDITION                                 | PART | SYMBOL               | MIN. | TYP. | MAX. | UNIT |  |
| INPUT                                   |  |      |                      |      |      |      |      |  |
| Forward voltage (2)                     | $I_F = 50 \text{ mA}$                          |      | V <sub>F</sub>       |      | 1.3  | 1.5  | V    |  |
| Reverse current (2)                     | V <sub>R</sub> = 3 V                           |      | I <sub>R</sub>       |      | 0.1  | 100  | μΑ   |  |
| Capacitance                             | $V_R = 0 V$                                    |      | Co                   |      | 25   |      | pF   |  |
| OUTPUT                                  |  |      |                      |      |      |      |      |  |
| Collector base breakdown voltage (2)    | $I_{C} = 100  \mu A$                           |      | BV <sub>CBO</sub>    | 70   |      |      | V    |  |
| Collector emitter breakdown voltage (2) | $I_C = 1 \text{ mA}$                           |      | BV <sub>CEO</sub>    | 30   |      |      | V    |  |
| Emitter collector breakdown voltage (2) | I <sub>E</sub> = 100 μA                        |      | BV <sub>ECO</sub>    | 7    |      |      | V    |  |
|   | V <sub>CE</sub> = 10 V, (base open)            | 4N25 |                      |      | 5    | 50   | nA   |  |
| L(dork) (2)                             |  | 4N26 |                      |      | 5    | 50   | nA   |  |
| I <sub>CEO</sub> (dark) (2)             |  | 4N27 |                      |      | 5    | 50   | nA   |  |
|   |  | 4N28 |                      |      | 10   | 100  | nA   |  |
| I <sub>CBO</sub> (dark) (2)             | V <sub>CB</sub> = 10 V,<br>(emitter open)      |      |                      |      | 2    | 20   | nA   |  |
| Collector emitter capacitance           | $V_{CE} = 0$                                   |      | C <sub>CE</sub>      |      | 6    |      | pF   |  |
| COUPLER                                 |  |      |                      |      |      |      |      |  |
| Isolation test voltage (2)              | Peak, 60 Hz                                    |      | V <sub>IO</sub>      | 5000 |      |      | V    |  |
| Saturation voltage, collector emitter   | $I_{CE} = 2 \text{ mA}, I_{F} = 50 \text{ mA}$ |      | V <sub>CE(sat)</sub> |      |      | 0.5  | V    |  |
| Resistance, input output (2)            | V <sub>IO</sub> = 500 V                        |      | R <sub>IO</sub>      | 100  |      |      | GΩ   |  |
| Capacitance, input output               | f = 1 MHz                                      |      | C <sub>IO</sub>      |      | 0.6  |      | рF   |  |

#### Notes

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

 $<sup>^{(1)}</sup>$  T<sub>amb</sub> = 25 °C, unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

 $<sup>^{(1)}</sup>$  T<sub>amb</sub> = 25 °C, unless otherwise specified.

<sup>(2)</sup> JEDEC registered values are 2500 V, 1500 V, 1500 V, and 500 V for the 4N25, 4N26, 4N27, and 4N28 respectively.

## Vishay Semiconductors Optocoupler, Phototransistor Output, with Base Connection



| CURRENT TRANSFER RATIO (1) |  |      |                   |      |      |      |      |
|----------------------------|--|------|-------------------|------|------|------|------|
| PARAMETER                  | TEST CONDITION                                 | PART | SYMBOL            | MIN. | TYP. | MAX. | UNIT |
| DC current transfer ratio  | V <sub>CE</sub> = 10 V, I <sub>F</sub> = 10 mA | 4N25 | CTR <sub>DC</sub> | 20   | 50   |      | %    |
|                            |  | 4N26 | CTR <sub>DC</sub> | 20   | 50   |      | %    |
|                            |  | 4N27 | CTR <sub>DC</sub> | 10   | 30   |      | %    |
|                            |  | 4N28 | CTR <sub>DC</sub> | 10   | 30   |      | %    |

#### Note

<sup>(1)</sup> Indicates JEDEC registered values.

| SWITCHING CHARACTERISTICS |  |                                 |      |      |      |      |  |
|---------------------------|--|---------------------------------|------|------|------|------|--|
| PARAMETER                 | TEST CONDITION                                       | SYMBOL                          | MIN. | TYP. | MAX. | UNIT |  |
| Rise and fall times       | $V_{CE}$ = 10 V, $I_F$ = 10 mA, $R_L$ = 100 $\Omega$ | t <sub>r</sub> , t <sub>f</sub> |      | 2    |      | μs   |  |

#### **TYPICAL CHARACTERISTICS**

T<sub>amb</sub> = 25 °C, unless otherwise specified

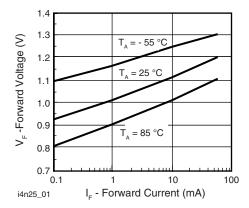


Fig. 1 - Forward Voltage vs. Forward Current

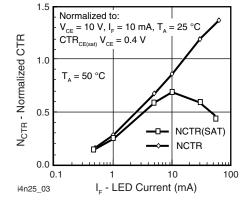


Fig. 3 - Normalized Non-Saturated and Saturated CTR vs. LED Current

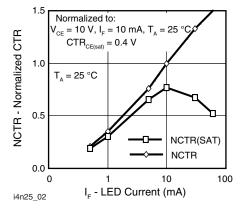


Fig. 2 - Normalized Non-Saturated and Saturated CTR vs. LED Current

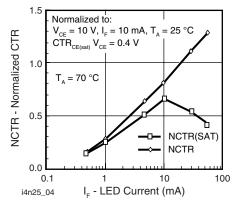


Fig. 4 - Normalized Non-Saturated and Saturated CTR vs. LED Current



## Optocoupler, Phototransistor Output, Vishay Semiconductors with Base Connection

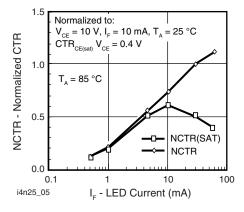


Fig. 5 - Normalized Non-Saturated and Saturated CTR vs. LED Current

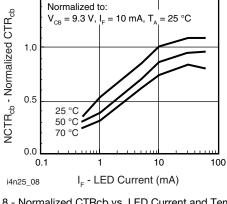


Fig. 8 - Normalized CTRcb vs. LED Current and Temperature

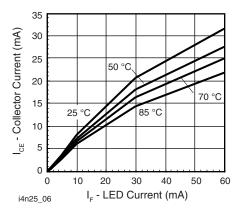


Fig. 6 - Collector Emitter Current vs. Temperature and LED Current

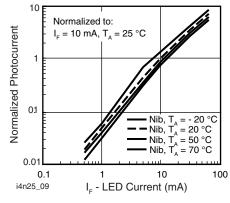


Fig. 9 - Normalized Photocurrent vs. I<sub>F</sub> and Temperature

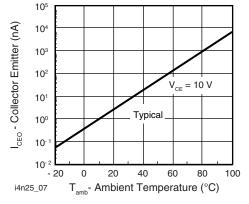


Fig. 7 - Collector Emitter Leakage Current vs. Temperature

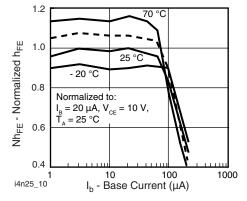


Fig. 10 - Normalized Non-Saturated h<sub>FE</sub> vs. Base Current and Temperature

## Vishay Semiconductors Optocoupler, Phototransistor Output, with Base Connection



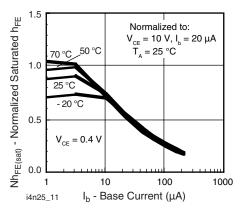


Fig. 11 - Normalized  $h_{\text{FE}}$  vs. Base Current and Temperature

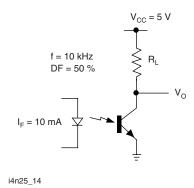


Fig. 14 - Switching Schematic

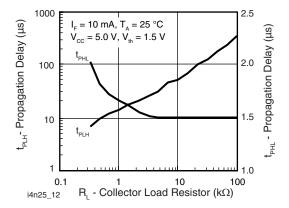


Fig. 12 - Propagation Delay vs. Collector Load Resistor

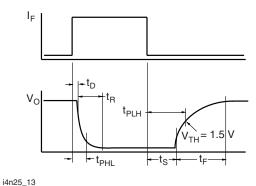
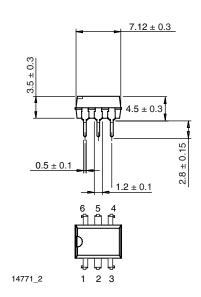


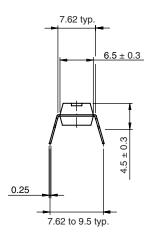
Fig. 13 - Switching Timing



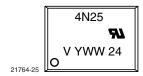
# Optocoupler, Phototransistor Output, Vishay Semiconductors with Base Connection

#### **PACKAGE DIMENSIONS** in millimeters





#### **PACKAGE MARKING**





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